



Docket No.: GR 98 P 2314 P

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By: J. P.

Date: 3/19/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Siegfried Schwarzl  
Applic. No. : 09/781,173  
Filed : February 12, 2001  
Title : Memory Cell Array And Method For Manufacturing It

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 4,455,626 (Lutes), dated June 19, 1984;

United States Patent No. 5,039,655 (Pisharody), dated August 13, 1991;

United States Patent No. 5,587,943 (Torok et al.), dated December 24, 1996;

European Patent Application EP 0 776 011 A2 (Chen et al.), dated May 28, 1997;

European Patent Application EP 0 776 011 A3 (Chen et al.), dated November 19, 1997;

European Patent Application EP 0875 901 A2 (Nishimura), dated November 4, 1998;

European Patent Application EP 0 875 901 A3 (Nishimura), dated November 3, 1999;



Japanese Patent Abstract JP 02 093 373 (Yoshino), dated April 4, 1990;

Japanese Patent Abstract JP 10 004 227 A (Gallagher et al.), dated January 6, 1998;

Japanese Patent Abstract JP 10 162 326 A (Perkin), dated June 19, 1998;

Japanese Patent Abstract JP 10 190 090 A (Papworth), dated July 21, 1998;

Mark H. Kryder et al.: "Magnetic Properties and Domain Structures in Narrow NiFe Stripes", IEEE Transactions on Magnetics, Vol. Mag-16, No. 1, January 1980, pp. 99-103;

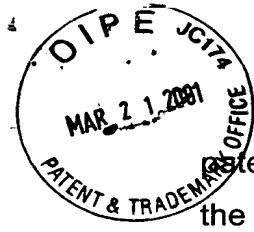
D.D. Tang et al.: "Spin-Valve RAM Cell", IEEE Transactions on Magnetics, Vol. 31, No. 6, November 1995, pp. 3206-3208;

J.M. Daughton: "Magnetic tunneling applied to memory (invited)", J. Appl. Phys. Vol. 81 No. 8, April 15, 1997, pp. 3758-3763;

Yu Lu et al.: "Shape-anisotropy-controlled magnetoresistive response in magnetic tunnel junctions", Appl. Phys. Lett. Vol. 70 No. 19, May 1997, pp. 2610-2612;

Haruki Yamane et al.: "Differential type giant magnetoresistive memory using spin-valve film with a NiO pinning layer", Journal of Applied Physics, Volume 83, No. 9, May 1, 1998, pp. 4862-4868.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications,



ents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,

M.P.  
For Applicant

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Date: March 19, 2001

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